



New Product

Si1012R/X
Vishay Siliconix

N-Channel 1.8-V (G-S) MOSFET

TrenchFET[®]
MOSFETs
1.8-V Rated



**ESD Protected
2000 V**

PRODUCT SUMMARY		
V _{DS} (V)	r _{DS(on)} (Ω)	I _D (mA)
20	0.70 @ V _{GS} = 4.5 V	600
	0.85 @ V _{GS} = 2.5 V	500
	1.25 @ V _{GS} = 1.8 V	350

FEATURES

- High-Side Switching
- Low On-Resistance: 0.7 Ω
- Low Threshold: 0.8 V (typ)
- Fast Switching Speed: 10 ns
- 1.8-V Operation
- Gate-Source ESD Protection

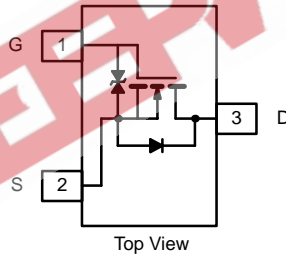
BENEFITS

- Ease in Driving Switches
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation

APPLICATIONS

- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories
- Battery Operated Systems
- Power Supply Converter Circuits
- Load/Power Switching Cell Phones, Pagers

SC-75A or SC-89



Ordering Information:

SC-75A (SOT-416):
Si1012R-Marking Code: C

SC-89 (SOT-490):
Si1012X-Marking Code: A

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	5 secs	Steady State	Unit	
Drain-Source Voltage	V _{DS}	20		V	
Gate-Source Voltage	V _{GS}	±6			
Continuous Drain Current (T _J = 150 °C) ^b	T _A = 25 °C	I _D	600	mA	
	T _A = 85 °C		400		
Pulsed Drain Current ^a		I _{DM}	1000		
Continuous Source Current (diode conduction) ^b		I _S	275	250	
Maximum Power Dissipation ^b for SC-75	T _A = 25 °C	P _D	175	150	mW
	T _A = 85 °C		90	80	
Maximum Power Dissipation ^b for SC-89	T _A = 25 °C		275	250	
	T _A = 85 °C		160	140	
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150		°C	
Gate-Source ESD Rating (HBM, Method 3015)	ESD	2000		V	

Notes

- Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board.

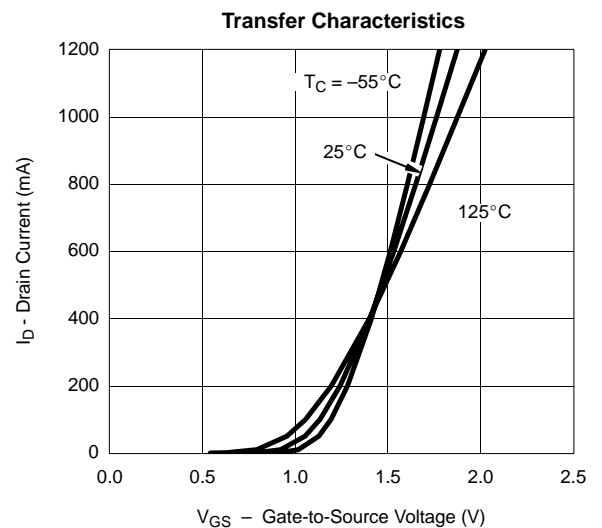
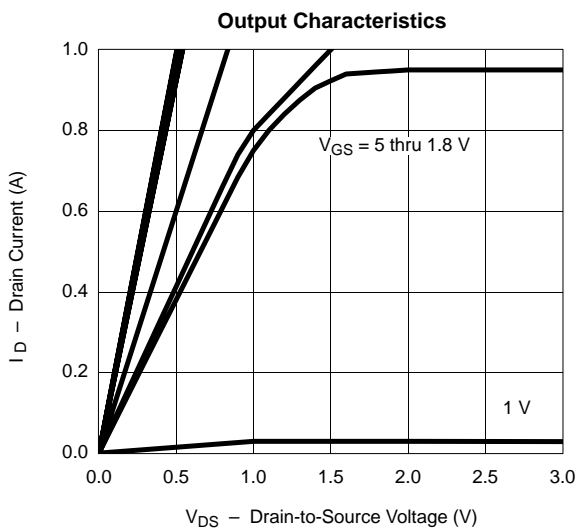


SPECIFICATIONS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	0.45			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±4.5 V		±0.5	±1.0	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 16 V, V _{GS} = 0 V		0.3	100	nA
		V _{DS} = 16 V, V _{GS} = 0 V, T _J = 85 °C			5	μA
On-State Drain Current ^a	I _{D(on)}	V _{DS} = 5 V, V _{GS} = 4.5 V	700			mA
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 4.5 V, I _D = 600 mA		0.41	0.70	Ω
		V _{GS} = 2.5 V, I _D = 500 mA		0.53	0.85	
		V _{GS} = 1.8 V, I _D = 350 mA		0.70	1.25	
Forward Transconductance ^a	g _{fs}	V _{DS} = 10 V, I _D = 400 mA		1.0		S
Diode Forward Voltage ^a	V _{SD}	I _S = 150 mA, V _{GS} = 0 V		0.8	1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = 10 V, V _{GS} = 4.5 V, I _D = 250 mA		750		pC
Gate-Source Charge	Q _{gs}			75		
Gate-Drain Charge	Q _{gd}			225		
Turn-On Delay Time	t _{d(on)}	V _{DD} = 10 V, R _L = 47 Ω I _D ≅ 200 mA, V _{GEN} = 4.5 V, R _G = 10 Ω		5		ns
Rise Time	t _r			5		
Turn-Off Delay Time	t _{d(off)}			25		
Fall Time	t _f			11		

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

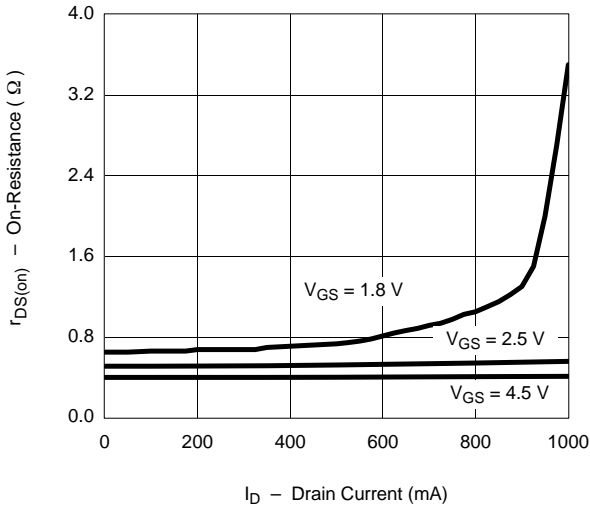
TYPICAL CHARACTERISTICS (T_A = 25 °C UNLESS NOTED)



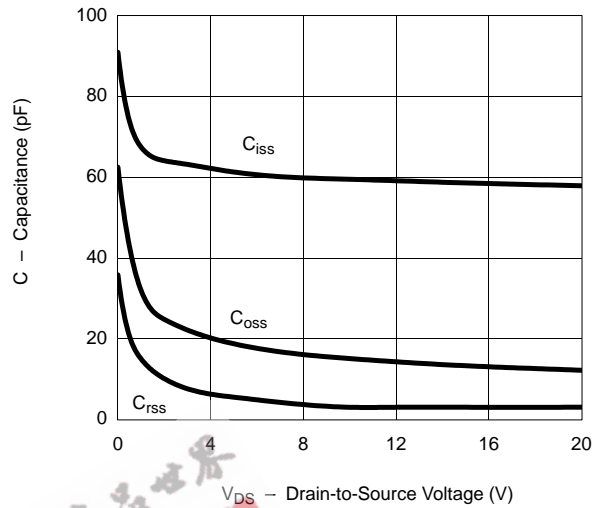


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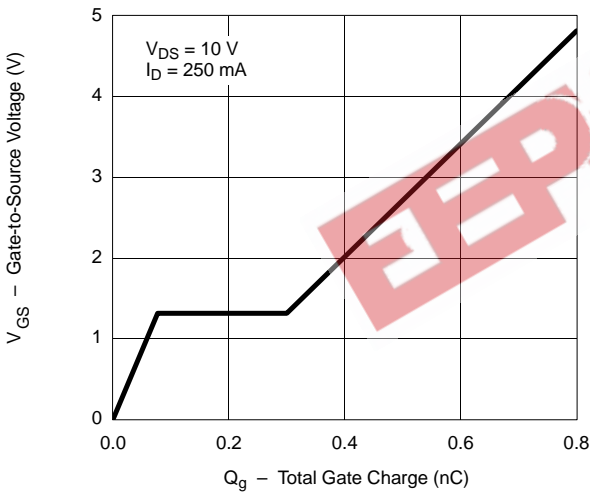
On-Resistance vs. Drain Current



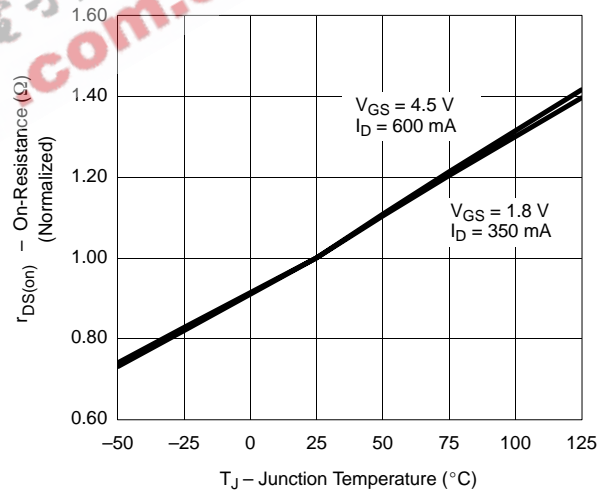
Capacitance



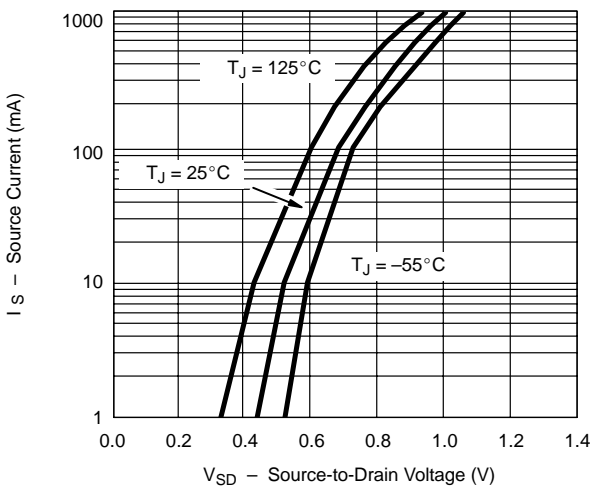
Gate Charge



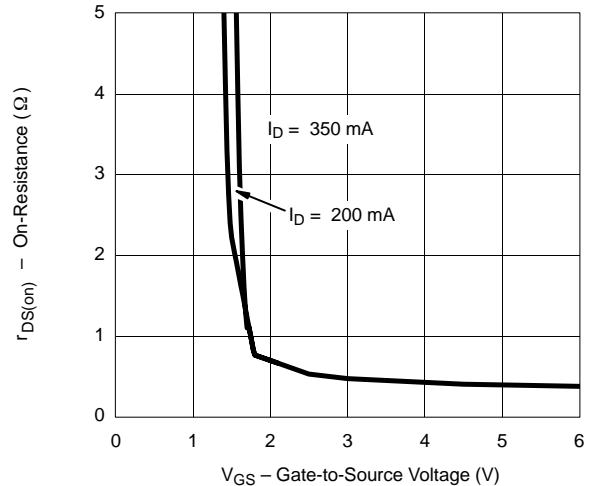
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

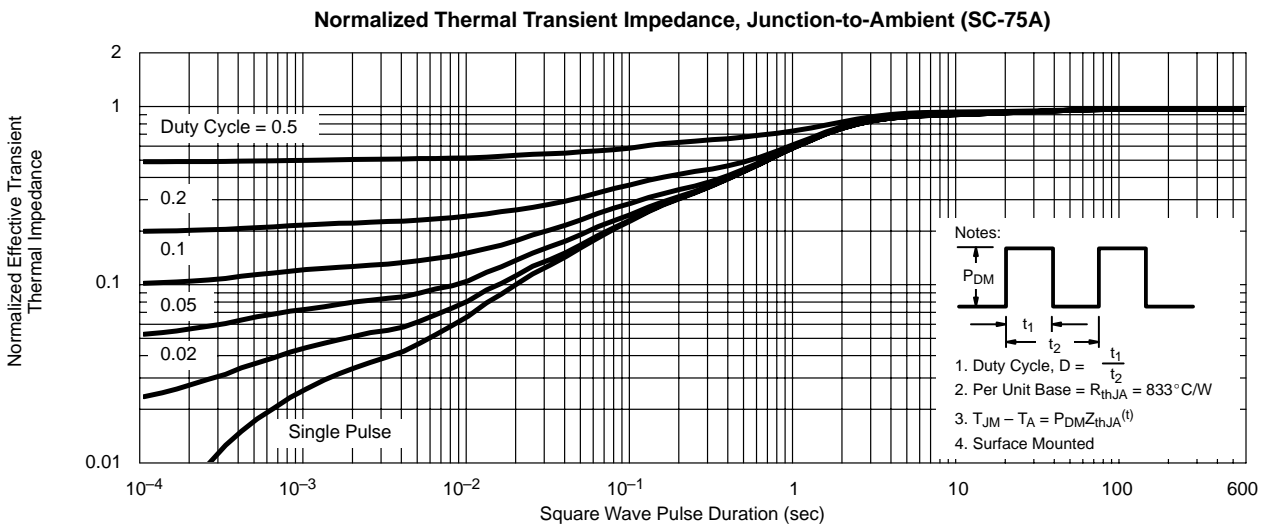
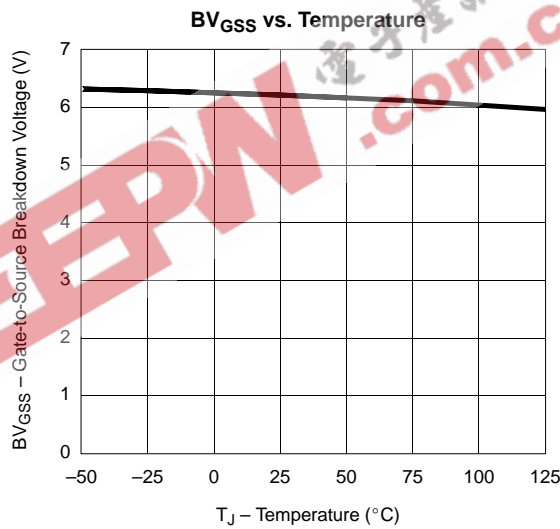
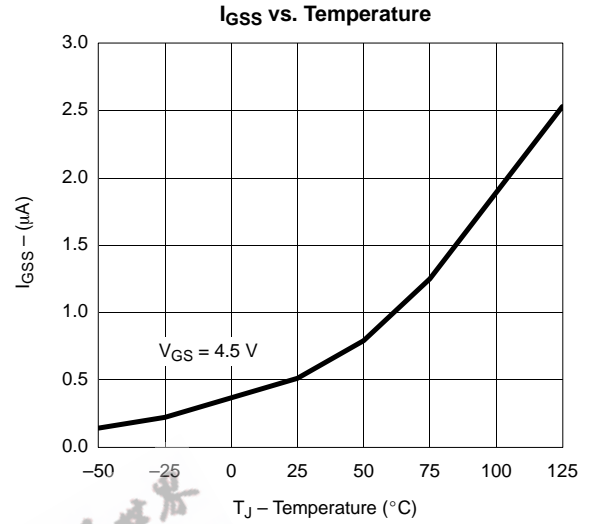
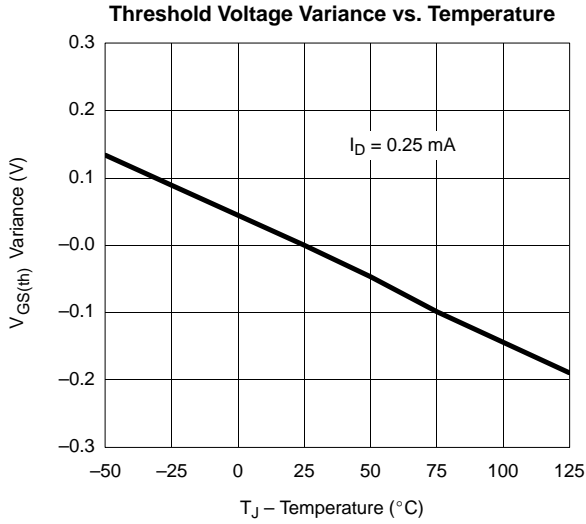


On-Resistance vs. Gate-to-Source Voltage



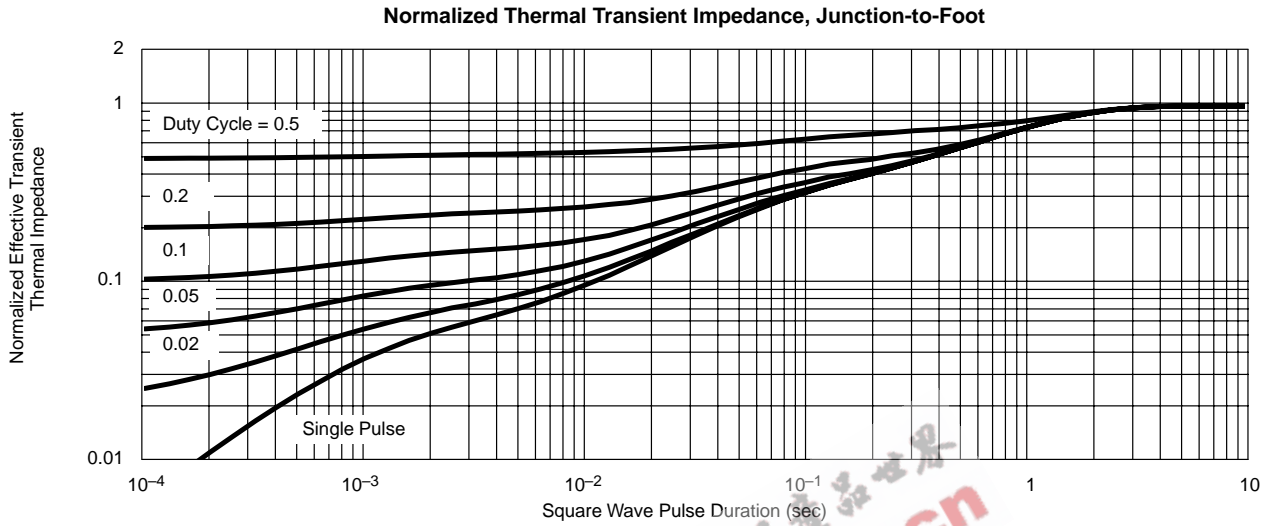


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS NOTED)





TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ UNLESS NOTED)



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